NSN 5961-01-005-6616

Semiconductor Device Set - Page 1 of 2



view Online at https://aerobasegroup.com/nsn/5961-01-005-6616
Inclosure Material:
Metal all transistor
Overall Length:
1.330 inches all transistor
Mounting Facility Quantity:
1 all transistor
Internal Configuration:
Junction contact all transistor
Internal Junction Configuration:
Npn all transistor
Component Function Relationship:
Matched
Component Name And Quantity:
2 transistor
Mounting Method:
Threaded stud all transistor
Overall Width Across Flats:
0.667 inches all transistor and 0.687 inches all transistor
Semiconductor Material:
Silicon all transistor
Voltage Rating In Volts Per Characteristic:
400.0 collector to base voltage/static/emitter open all transistor and 400.0 collector to emitter voltage/static/base open all transistor and 6.5
emitter to base voltage, static, collector open all transistor
Current Rating Per Characteristic:
10.00 amperes source cutoff current all transistor
Power Rating Per Characteristic:
100.0 watts small-signal input power, common-collector absolute all transistor
Maximum Operating Tempurature Per Measurement Point:
150.0 degrees celsius ambient air all transistor
Precious Material And Location:
Die attach with header and cap option gold
Precious Material:
Gold
Test Data Document:
82577-928272 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.;
excludes any specification, standard or other document that may be referenced in a basic governing drawing)
Terminal Type And Quantity:
3 tab, solder lug all transistor
Shelf Life:
N/a
Unit Of Measure:

No

Demilitarization:

NSN 5961-01-005-6616

Semiconductor Device Set - Page 2 of 2



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